

45. A method according to claim 42, wherein a second liquid is supplied during said further polishing.

46. A method according to claim 45, wherein said second liquid comprises a slurry containing abrasive particles.

47. A method according to claim 42, wherein the object is semiconductor wafer having raised and depressed patterns thereon.

48. A polishing apparatus for polishing a surface of a substrate comprising:
an abrading surface comprising abrasive particles and binder for binding said abrasive particles;

top ring for holding the substrate against said abrading surface;
a second polishing surface comprising polishing cloth; and
a liquid supply device for supplying a liquid not containing abrasive particles to said abrading surface.

49. An apparatus according to claim 48, wherein said first liquid comprises water or active solution.

50. An apparatus according to claim 48, wherein said first liquid comprises ionized water.

51. An apparatus according to claim 48, wherein a second liquid is supplied during said second polishing process.

52. An apparatus according to claim 49, wherein said second liquid comprises a slurry containing abrasive particles.

53. An apparatus according to claim 48, wherein said object is semiconductor wafer
having raised and depressed patterns thereon.